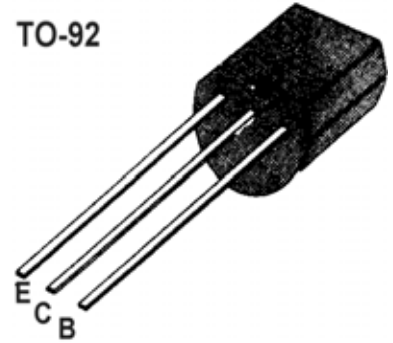


■■ APPLICATION: LOW FREQUENCY AMPLIFIER APPLICATION.

■■ MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_c	-150	mA
Collector Power Dissipation	P_c	400	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55~150	$^\circ\text{C}$

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■■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Common Emitter DC Current Gain	h_{FE}	70		400		$V_{CE}=-6V, I_c=-2mA$
Collector Cut-off Current	I_{CBO}			-0.1	μA	$V_{CB}=-50V, I_E=0$
Emitter Cut-off Current	I_{EBO}			-0.1	μA	$V_{EB}=-5V, I_c=0$
Collector-Base Breakdown Voltage	BV_{CBO}	-50			V	$I_c=-0.02mA, I_E=0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	-50			V	$I_c=-1mA, I_B=0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	$I_E=-0.02mA, I_c=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.1	-0.3	V	$I_c=-100mA, I_B=-10mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.1	V	$I_c=-100mA, I_B=-10mA$
Gain bandwidth product	f_T	80			MHz	$I_c=-1mA, V_{CE}=-10V$
Common Base Output Capacitance	C_{ob}		4	7	PF	$V_{CB}=-10V, I_E=0, f=1MHz$
Noise Figure	N_F		1.0	10	dB	$V_{CE}=-6V, I_c=-0.1mA, f=1MHz, R_g=10K\Omega$

■■ h_{FE} Classification And Marking

Classification	O	Y	GR
h_{FE}	70~140	120~240	200~400